



# DG411HS/412HS/413HS

Vishay Siliconix

## Precision Monolithic Quad SPST CMOS Analog Switches

### DESCRIPTION

The DG411HS series of monolithic quad analog switches was designed to provide high speed, low error switching of precision analog signals. Combining low power (0.35  $\mu$ W) with high speed ( $t_{ON}$ : 68 ns), the DG411HS family is ideally suited for portable and battery powered industrial and military applications.

To achieve high-voltage ratings and superior switching performance, the DG411HS series was built on Vishay Siliconix's high voltage silicon gate process. An epitaxial layer prevents latchup.

Each switch conducts equally well in both directions when on, and blocks input voltages up to the supply levels when off.

The DG411HS and DG412HS respond to opposite control logic as shown in the Truth Table. The DG413HS has two normally open and two normally closed switches.

### FEATURES

- 44 V Supply Max Rating
- $\pm 15$  V Analog Signal Range
- On-Resistance -  $r_{DS(on)}$ : 25  $\Omega$
- Fast Switching -  $t_{ON}$ : 68 ns
- Ultra Low Power -  $P_D$ : 0.35  $\mu$ W
- TTL, CMOS Compatible
- Single Supply Capability



**RoHS\***  
COMPLIANT

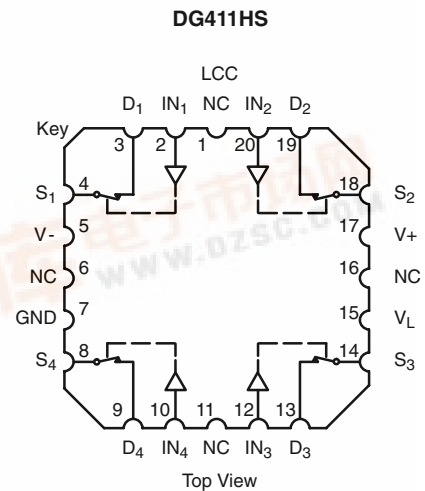
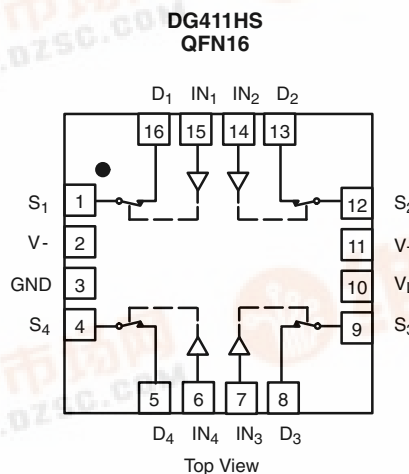
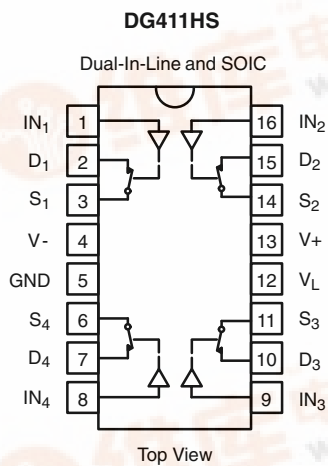
### BENEFITS

- Widest Dynamic Range
- Low Signal Errors and Distortion
- Break-Before-Make Switching Action
- Simple Interfacing

### APPLICATIONS

- Precision Automatic Test Equipment
- Precision Data Acquisition
- Communication Systems
- Battery Powered Systems
- Computer Peripherals

### FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE		
Logic	DG411HS	DG412HS
0	ON	OFF
1	OFF	ON

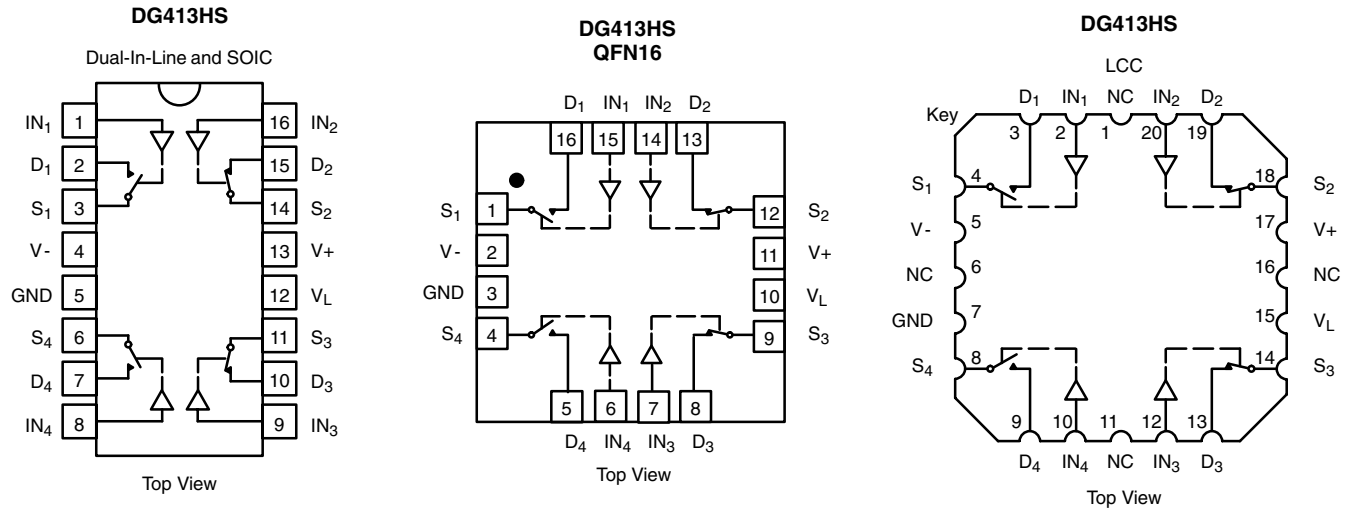
\* Pb containing terminations are not RoHS compliant, exemptions may apply

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## FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE		
Logic	SW <sub>1</sub> , SW <sub>4</sub>	SW <sub>2</sub> , SW <sub>3</sub>
0	OFF	ON
1	ON	OFF

ORDERING INFORMATION		
Temp Range	Package	Part Number
<b>DG411HS/412HS</b>		
- 40 to 85 °C	16-Pin Plastic DIP	DG411HSDJ DG411HSDJ-E3
		DG412HSDJ DG412HSDJ-E3
	16-Pin Narrow SOIC	DG411HSDY DG411HSDY-E3 DG411HSDY-T1 DG411HSDY-T1-E3
		DG412HSDY DG412HSDY-E3 DG412HSDY-T1 DG412HSDY-T1-E3
		DG411HSDN-T1-E4 DG412HSDN-T1-E4
	16-Pin QFN 4 x 4 mm	
<b>DG413HS</b>		
- 40 to 85 °C	16-Pin Plastic DIP	DG413HSDJ DG413HSDJ-E3
	16-Pin Narrow SOIC	DG413HSDY DG413HSDY-E3 DG413HSDY-T1 DG413HSDY-T1-E3
	16-Pin QFN 4 x 4 mm	DG413HSDN-T1-E4



ABSOLUTE MAXIMUM RATINGS			
Parameter		Limit	Unit
V+ to V-		44	V
GND to V-		25	
V <sub>L</sub>		(GND - 0.3) to (V+) + 0.3	
Digital Inputs <sup>a</sup> , V <sub>S</sub> , V <sub>D</sub>		(V-) - 2 to (V+) + 2 or 30 mA, whichever occurs first	
Continuous Current (Any Terminal)		30	mA
Peak Current, S or D (Pulsed 1 ms, 10 % Duty Cycle)		100	
Storage Temperature	(AK, AZ Suffix)	- 65 to 150	°C
	(DJ, DY, DN Suffix)	- 65 to 125	
Power Dissipation (Package) <sup>b</sup>	16-Pin Plastic DIP <sup>c</sup>	470	mW
	16-Pin Narrow SOIC <sup>d</sup>	600	
	16-Pin CerDIP <sup>e</sup>	900	
	LCC-20 <sup>e</sup>	900	
	16-Pin (4 x 4 mm) QFN <sup>f</sup>	1880	

Notes:

- a. Signals on S<sub>x</sub>, D<sub>x</sub>, or IN<sub>x</sub> exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- b. All leads welded or soldered to PC Board.
- c. Derate 6 mW/°C above 25 °C.
- d. Derate 7.6 mW/°C above 75 °C.
- e. Derate 12 mW/°C above 75 °C.
- f. Derate 23.5 mW/°C above 70 °C.

SPECIFICATIONS <sup>a</sup>									
Parameter	Symbol	Test Conditions Unless Specified V+ = 15 V, V- = - 15 V V <sub>L</sub> = 5 V, V <sub>IN</sub> = 2.4 V, 0.8 V <sup>f</sup>	Temp <sup>b</sup>	Typ <sup>c</sup>	A Suffix - 55 to 125 °C		D Suffix - 40 to 85 °C		Unit
					Min <sup>d</sup>	Max <sup>d</sup>	Min <sup>d</sup>	Max <sup>d</sup>	
<b>Analog Switch</b>									
Analog Signal Range <sup>e</sup>	V <sub>ANALOG</sub>		Full		- 15	15	- 15	15	V
Drain-Source On-Resistance	r <sub>DS(on)</sub>	V+ = 13.5 V, V- = - 13.5 V I <sub>S</sub> = - 10 mA, V <sub>D</sub> = ± 8.5 V	Room Full	25		35 45		35 45	Ω
Switch Off Leakage Current	I <sub>S(off)</sub>	V+ = 16.5 V, V- = - 16.5 V V <sub>D</sub> = ± 15.5 mA, V <sub>S</sub> = ± 15.5 V	Room Full	± 0.1	- 0.25 - 20	0.25 20	- 0.25 - 5	0.25 5	nA
	I <sub>D(off)</sub>		Room Full	± 0.1	- 0.25 - 20	0.25 20	- 0.25 - 5	0.25 5	
Channel On Leakage Current	I <sub>D(on)</sub>	V+ = 16.5 V, V- = - 16.5 V V <sub>D</sub> = V <sub>S</sub> = ± 15.5 V	Room Full	± 0.1	- 0.4 - 40	0.4 40	- 0.4 - 10	0.4 10	
<b>Digital Control</b>									
Input Current, V <sub>IN</sub> Low	I <sub>IL</sub>	V <sub>IN</sub> Under Test = 0.8 V	Full	0.005	- 0.5	0.5	- 0.5	0.5	μA
Input Current, V <sub>IN</sub> High	I <sub>IH</sub>	V <sub>IN</sub> Under Test = 2.4 V	Full	0.005	- 0.5	0.5	- 0.5	0.5	
Input Capacitance <sup>e</sup>	C <sub>IN</sub>	f = 1 MHz	Room	5					pF
<b>Dynamic Characteristics</b>									
Turn-On Time	t <sub>ON</sub>	R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 35 pF V <sub>S</sub> = ± 10 V, See Figure 2	Room Full	68		105 127		105 116	ns
Turn-Off Time	t <sub>OFF</sub>		Room Full	42		80 94		80 90	
Break-Before-Make Time Delay	t <sub>D</sub>	DG413HS Only, V <sub>S</sub> = 10 V R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 35 pF	Room	20					
Charge Injection <sup>e</sup>	Q	V <sub>g</sub> = 0 V, R <sub>g</sub> = 0 Ω, C <sub>L</sub> = 10 nF	Room	22					pC

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SPECIFICATIONS <sup>a</sup>									
Parameter	Symbol	Test Conditions Unless Specified V <sub>+</sub> = 15 V, V <sub>-</sub> = -15 V V <sub>L</sub> = 5 V, V <sub>IN</sub> = 2.4 V, 0.8 V <sup>f</sup>	Temp <sup>b</sup>	Typ <sup>c</sup>	A Suffix - 55 to 125 °C		D Suffix - 40 to 85 °C		Unit
					Min <sup>d</sup>	Max <sup>d</sup>	Min <sup>d</sup>	Max <sup>d</sup>	
<b>Dynamic Characteristics (Cont'd)</b>									
Off Isolation <sup>e</sup>	OIRR	R <sub>L</sub> = 50 Ω, C <sub>L</sub> = 5 pF f = 1 MHz	Room	- 91					dB
Channel-to-Channel Crosstalk <sup>e</sup>	X <sub>TALK</sub>		Room	- 88					
Source Off Capacitance <sup>e</sup>	C <sub>S(off)</sub>	f = 1 MHz	Room	12					pF
Drain Off Capacitance <sup>e</sup>	C <sub>D(off)</sub>		Room	12					
Channel On Capacitance <sup>e</sup>	C <sub>D(on)</sub>		Room	30					
<b>Power Supplies</b>									
Positive Supply Current	I <sub>+</sub>	V <sub>+</sub> = 16.5 V, V <sub>-</sub> = -16.5 V V <sub>IN</sub> = 0 or 5 V	Room Full	0.0001		1 5		1 5	μA
Negative Supply Current	I <sub>-</sub>		Room Full	- 0.0001	- 1 - 5		- 1 - 5		
Logic Supply Current	I <sub>L</sub>		Room Full	0.0001		1 5		1 5	
Ground Current	I <sub>GND</sub>		Room Full	- 0.0001	- 1 - 5		- 1 - 5		

SPECIFICATIONS <sup>a</sup> FOR UNIPOLAR SUPPLIES									
Parameter	Symbol	Test Conditions Unless Specified V <sub>+</sub> = 12 V, V <sub>-</sub> = 0 V V <sub>L</sub> = 5 V, V <sub>IN</sub> = 2.4 V, 0.8 V <sup>f</sup>	Temp <sup>b</sup>	Typ <sup>c</sup>	A Suffix - 55 to 125 °C		D Suffix - 40 to 85 °C		Unit
					Min <sup>d</sup>	Max <sup>d</sup>	Min <sup>d</sup>	Max <sup>d</sup>	
<b>Analog Switch</b>									
Analog Signal Range <sup>e</sup>	V <sub>ANALOG</sub>		Full			12		12	V
Drain-Source On-Resistance	r <sub>DS(on)</sub>	V <sub>+</sub> = 10.8 V, I <sub>S</sub> = -10 mA V <sub>D</sub> = 3 V, 8 V	Room Full	49		80 100		80 100	Ω
<b>Dynamic Characteristics</b>									
Turn-On Time	t <sub>ON</sub>	R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 35 pF V <sub>S</sub> = 8 V, See Figure 2	Room Hot	95		140 180		140 160	ns
Turn-Off Time	t <sub>OFF</sub>		Room Hot	36		70 79		70 74	
Break-Before-Make Time Delay	t <sub>D</sub>	DG413HS Only, V <sub>S</sub> = 8 V R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 35 pF	Room	60					
Charge Injection	Q	V <sub>g</sub> = 6 V, R <sub>g</sub> = 0 Ω, C <sub>L</sub> = 1 nF	Room	60					pC
<b>Power Supplies</b>									
Positive Supply Current	I <sub>+</sub>	V <sub>+</sub> = 13.2 V, V <sub>IN</sub> = 0 or 5 V	Room Hot	0.0001		1 5		1 5	μA
Negative Supply Current	I <sub>-</sub>		Room Hot	- 0.0001	- 1 - 5		- 1 - 5		
Logic Supply Current	I <sub>L</sub>		Room Hot	0.0001		1 5		1 5	
Ground Current	I <sub>GND</sub>		Room Hot	- 0.0001	- 1 - 5		- 1 - 5		

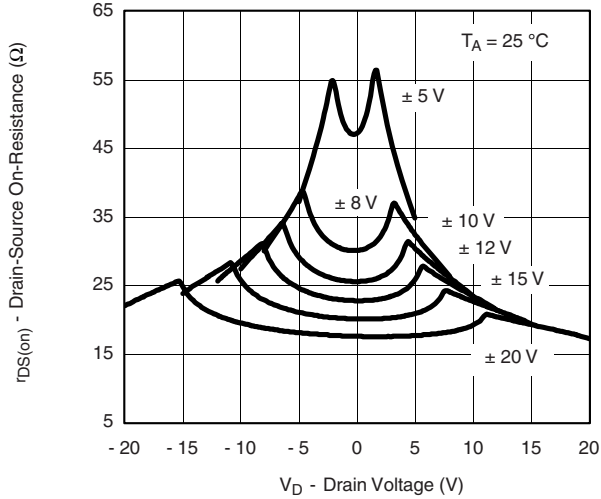
Notes:

- Refer to PROCESS OPTION FLOWCHART.
- Room = 25 °C, Full = as determined by the operating temperature suffix.
- Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- Guaranteed by design, not subject to production test.
- V<sub>IN</sub> = input voltage to perform proper function.

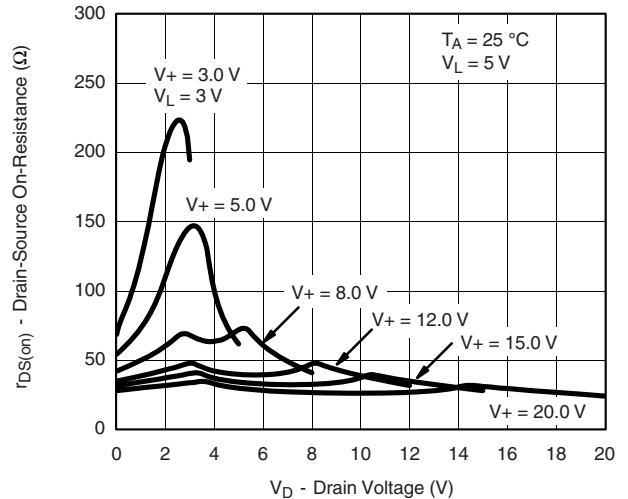
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



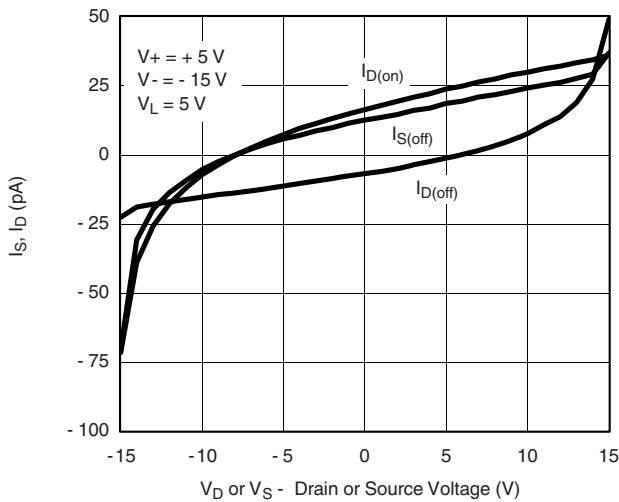
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



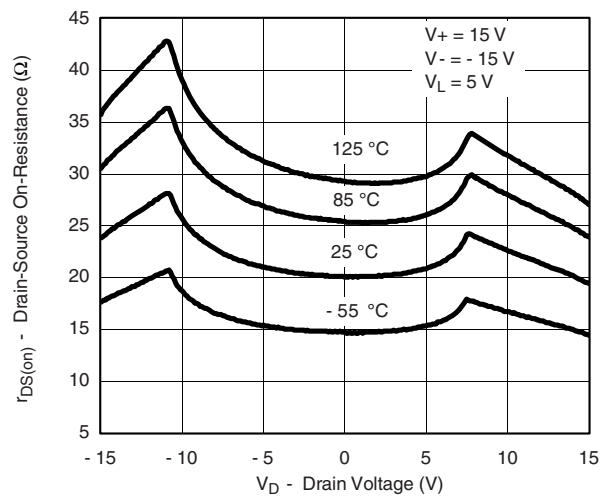
**On-Resistance vs.  $V_D$  and Dual Supply Voltage**



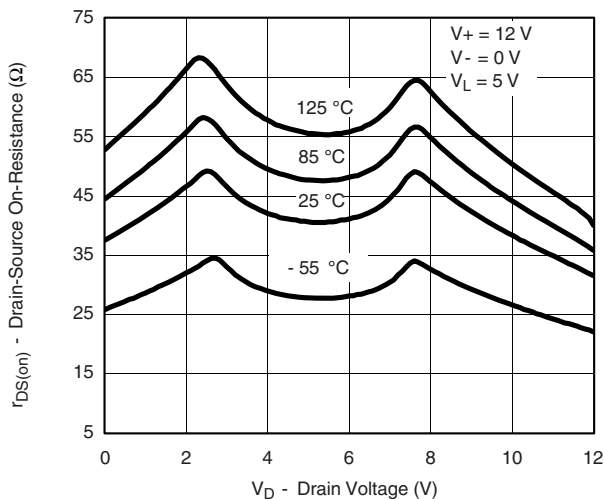
**On-Resistance vs.  $V_D$  and Unipolar Supply Voltage**



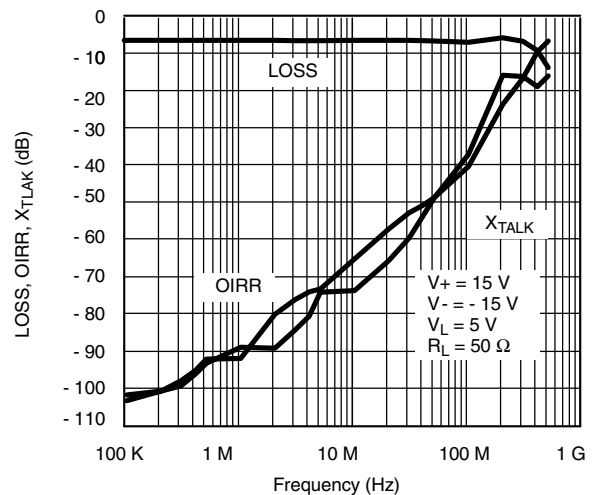
**Leakage Current vs. Analog Voltage**



**On-Resistance vs.  $V_D$  and Temperature**



**On-Resistance vs.  $V_D$  and Temperature**



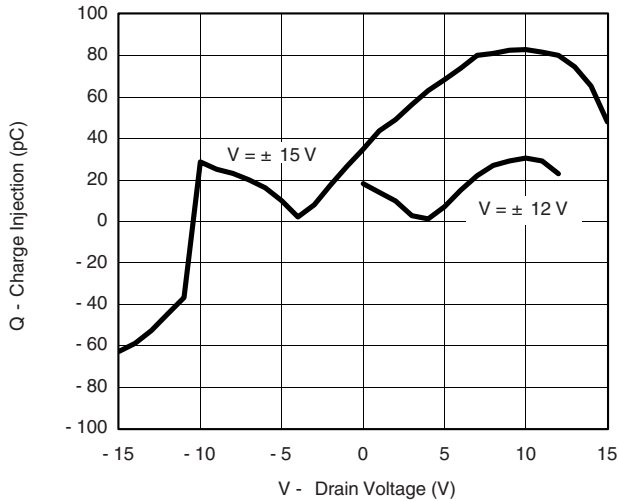
**Insertion Loss, Off-Isolation, Crosstalk vs. Frequency**

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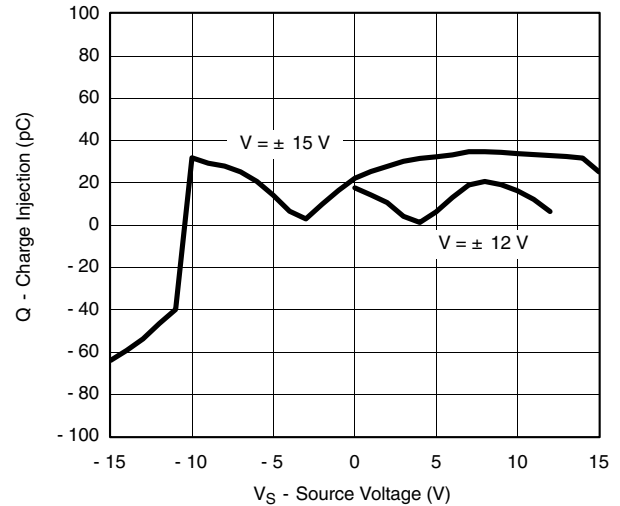
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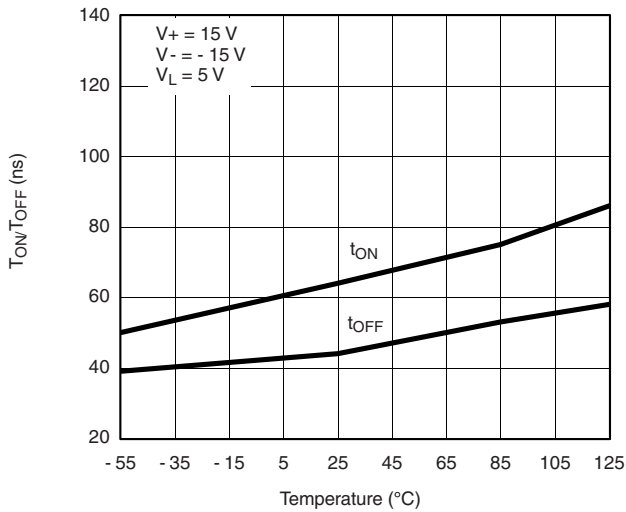
## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



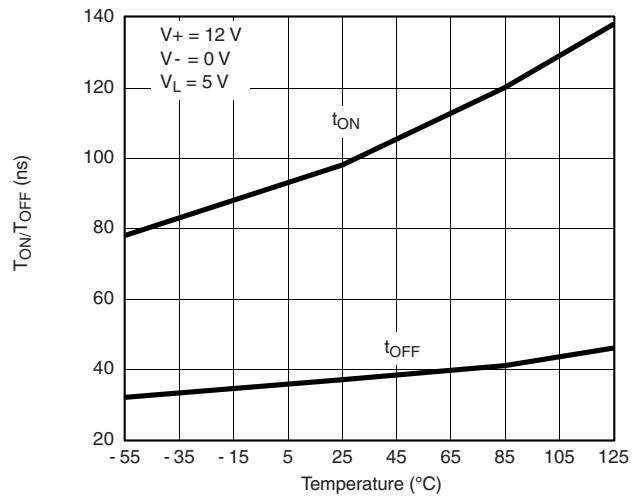
Charge Injection vs. Analog Voltage



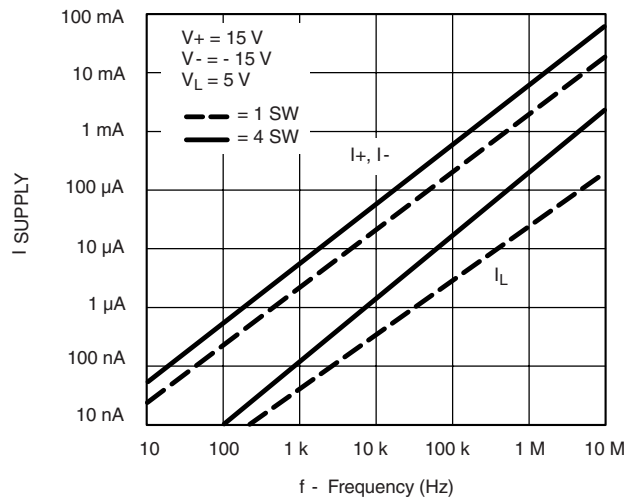
Charge Injection vs. Analog Voltage



Switching Time vs. Temperature



Switching Time vs. Temperature



Supply Current vs. Input Switching Frequency

## SCHEMATIC DIAGRAM (TYPICAL CHANNEL)

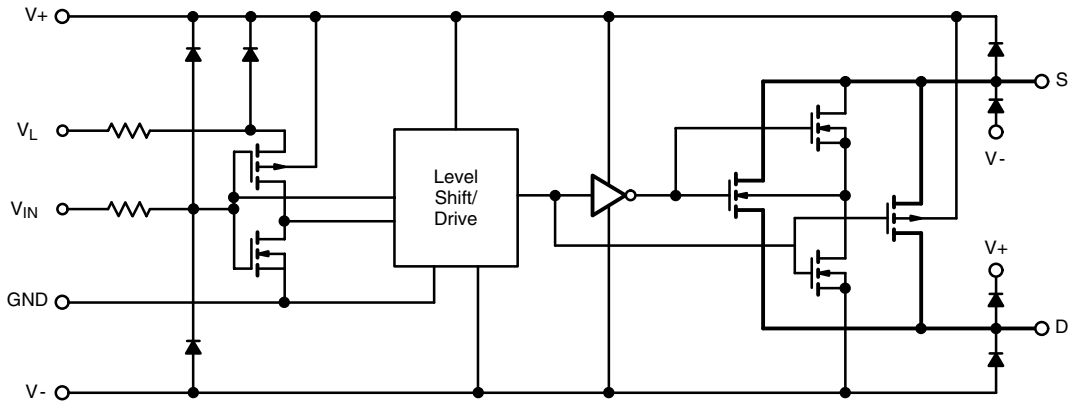
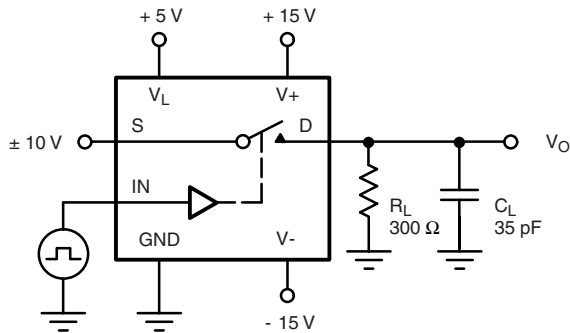


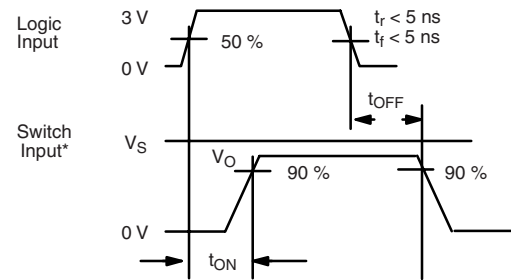
Figure 1.

## TEST CIRCUITS



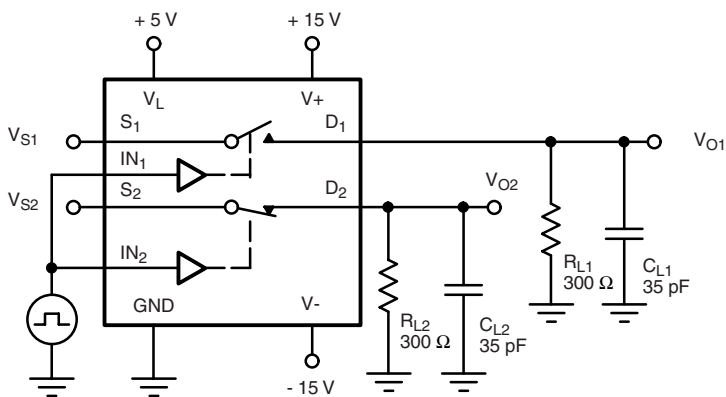
$C_L$  (includes fixture and stray capacitance)

$$V_O = V_S \frac{R_L}{R_L + r_{DS(on)}}$$



Note: Logic input waveform is inverted for switches that have the opposite logic sense control

Figure 2. Switching Time



$C_L$  (includes fixture and stray capacitance)

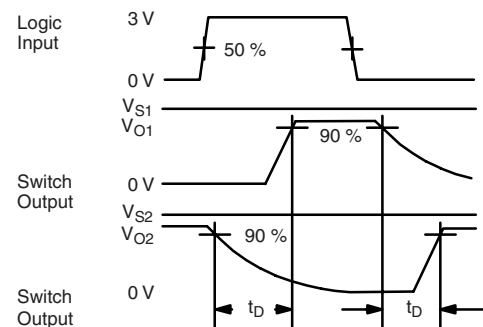


Figure 3. Break-Before-Make (DG413HS)

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## TEST CIRCUITS

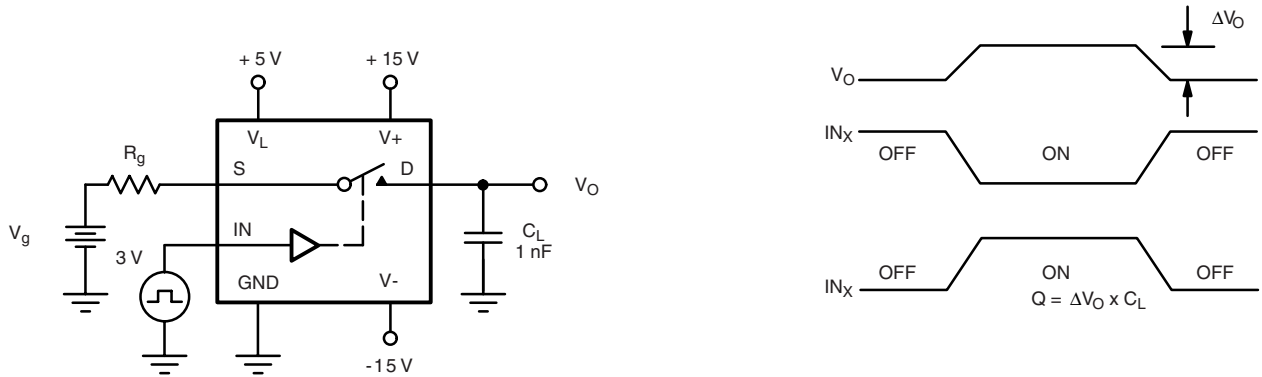


Figure 4. Charge Injection

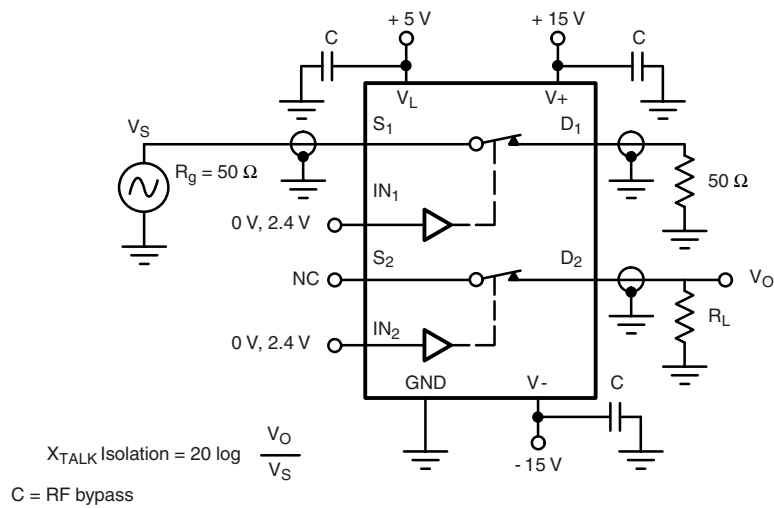


Figure 5. Crosstalk

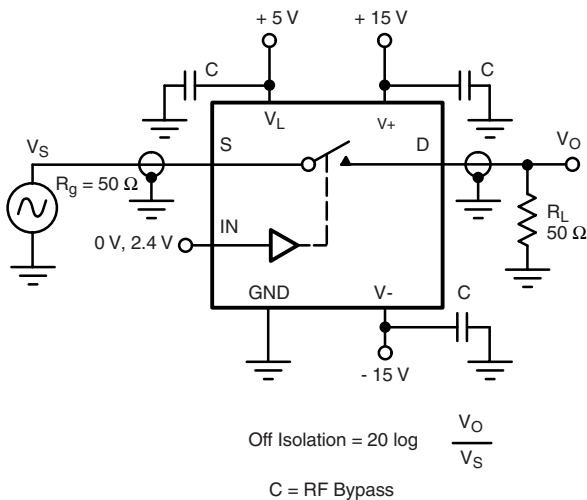


Figure 6. Off-Isolation

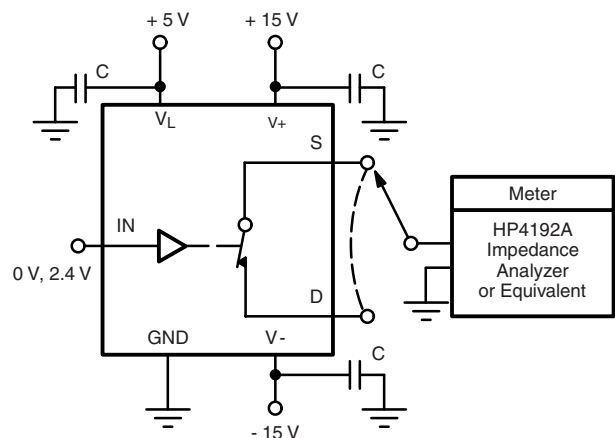


Figure 7. Source/Drain Capacitances

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <http://www.vishay.com/ppg?72053>.





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